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November 2013

## FQPF27N25

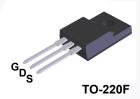
# N-Channel QFET<sup>®</sup> MOSFET 250 V, 14 A, 110 m $\Omega$

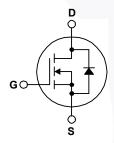
### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- 14 A, 250 V,  $R_{DS(on)}$  = 110 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 7 A
- Low Gate Charge (Typ. 50 nC)
- · Low Crss (Typ. 45 pF)
- · 100% Avalanche Tested





## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQPF27N25	Unit	
V <sub>DSS</sub>	Drain-Source Voltage		250	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		14	А	
	- Continuous (T <sub>C</sub> = 100°C)		8.9	А	
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	56	Α	
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	600	mJ	
I <sub>AR</sub>	Avalanche Current	(Note 1)	14	A	
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	5.5	mJ	
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns	
$P_D$	Power Dissipation (T <sub>C</sub> = 25°C)		55	W	
	- Derate above 25°C		0.44	W/°C	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C	

## **Thermal Characteristics**

Symbol	Parameter	FQPF27N25	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.27	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

## **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQPF27N25	FQPF27N25	TO-220F	Tube	N/A	N/A	50 units

## **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	250			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.29		V/°C
I <sub>DSS</sub>	nes	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V			1	μΑ
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200 V, T <sub>C</sub> = 125°C			10	μA	
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nA
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 7.0 A		0.083	0.11	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 7.0 A		15		S
Dynam	ic Characteristics					
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz		1900	2450	pF
C <sub>oss</sub>	Output Capacitance			360	470	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			45	60	pF
Switch	ing Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	$V_{DD} = 125 \text{ V}, I_{D} = 27 \text{ A},$ $R_{G} = 25 \Omega$		32	75	ns
t <sub>r</sub>	Turn-On Rise Time			270	550	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			80	170	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	120	250	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 200 V, I <sub>D</sub> = 27 A,		50	65	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10 V	/	12.5		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		26	- /	nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				14	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				56	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 14 A			1.5	V
			1			

## $Q_{rr}$

 $t_{rr}$ 

- Notes: Notes: Notes: All the Notes: All the Notes: All the Notes: Pulse width limited by maximum junction temperature. 
  2. L = 4.9 mH, I  $_{AS}$  = 14 A, V  $_{DD}$  = 50 V, R  $_{G}$  = 25  $\Omega$ , starting T  $_{J}$  = 25°C. 
  3. I  $_{SD}$   $\leq$  27 A, di/dt  $\leq$  300 A/µs, V  $_{DD}$   $\leq$  BV  $_{DSS}$ , starting T  $_{J}$  = 25°C. 
  4. Essentially independent of operating temperature.

Reverse Recovery Time

Reverse Recovery Charge

ns

μС

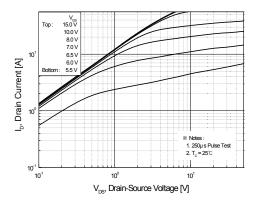
220

1.8

 $V_{GS} = 0 \text{ V, } I_{S} = 27 \text{ A,}$ 

 $dI_F / dt = 100 A/\mu s$ 

## **Typical Characteristics**

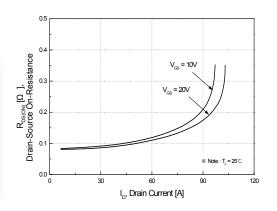


Y 10<sup>1</sup> 2 4 6 8 10

V<sub>SS</sub> , Gate-Source Voltage [V]

Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



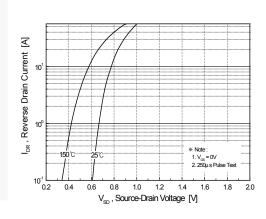
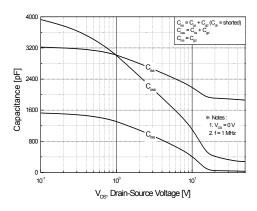


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



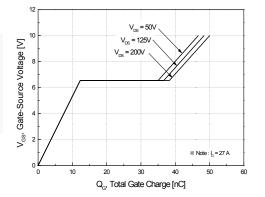


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

## Typical Characteristics (continued)

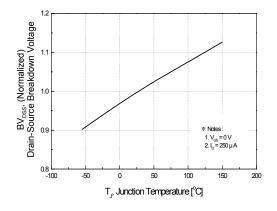
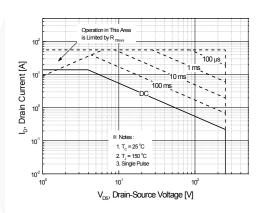


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



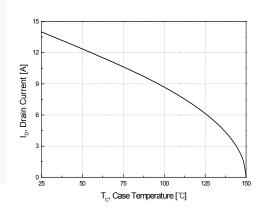


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

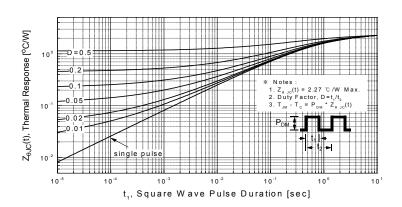


Figure 11. Transient Thermal Response Curve

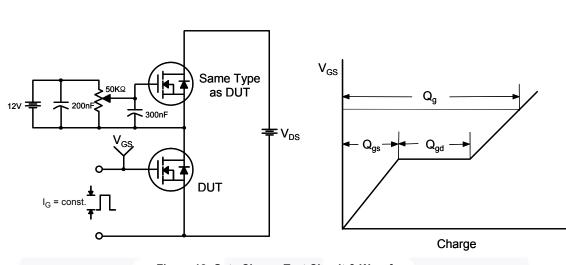


Figure 12. Gate Charge Test Circuit & Waveform

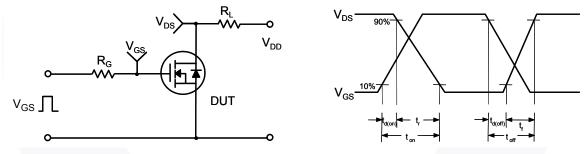


Figure 13. Resistive Switching Test Circuit & Waveforms

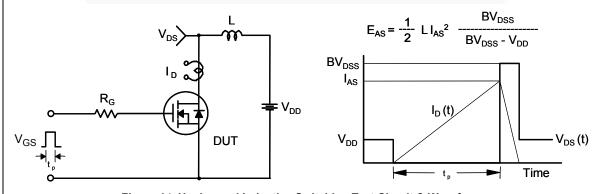
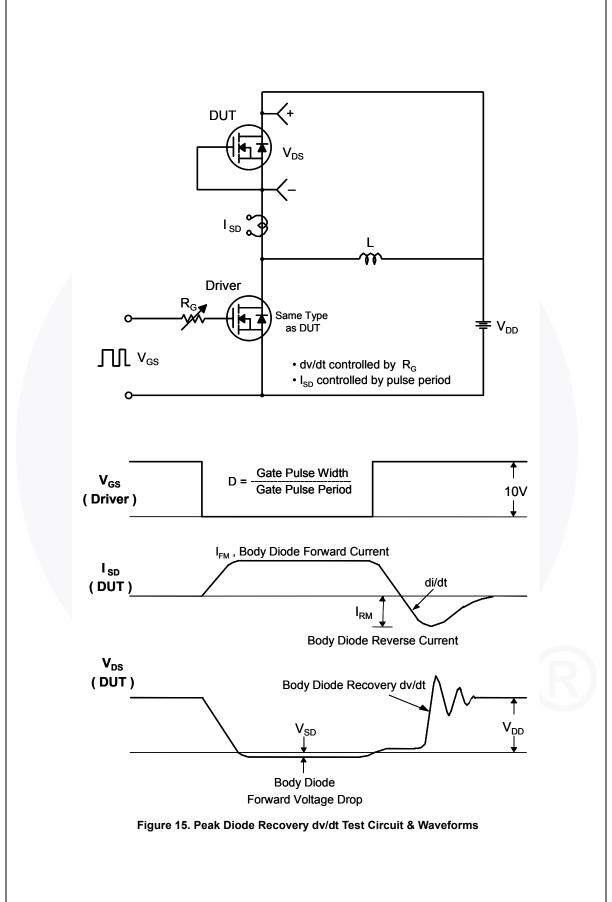


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



## **Mechanical Dimensions**

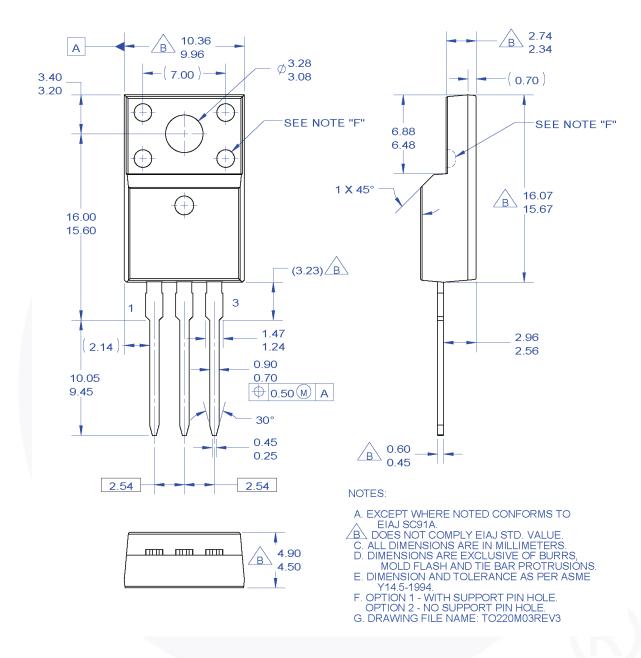


Figure 16. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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